IN THE CLAIMS

Please amend the claims as follows:

Claims 1-4 (Canceled).

5. (Currently Amended) A magnetic memory comprising:

a word line;

a bit line intersecting the word line; and

a memory cell positioned in an intersection portion of the word and bit lines and including a magnetoresistance element, the magnetoresistance element comprising:

a free layer comprising a first ferromagnetic layer and a second ferromagnetic layer which face each other and whose magnetization directions are equal to each other, and a nonmagnetic film which intervenes between the first and second ferromagnetic layers, the free layer being changeable in the magnetization directions on applying a magnetic field;

a first pinned layer comprising a third ferromagnetic layer which faces the free layer, the first pinned layer retaining a magnetization direction thereof on applying the magnetic field; and

a first nonmagnetic layer intervening between the free layer and the first pinned layer,

~~wherein the nonmagnetic film is a layer selected from the group consisting of a first layer made of molybdenum and having a thickness of 0.8 nm to 1.2 nm, a second layer~~

wherein the nonmagnetic film is a layer selected from the group consisting of a first layer made of molybdenum and having a thickness of 0.8 nm to 1.2 nm, a second layer made of rhenium and having a thickness of 1.4 nm to 1.8 nm, a third layer made of tungsten and having a thickness of 0.8 nm to 1.2 nm, and a fourth layer made of niobium and having a thickness of 1.4 nm to 1.8 nm.

Claims 6-9 (Canceled).

10. (Previously Presented) A magnetic memory comprising:

a word line;

a bit line intersecting the word line; and

a memory cell positioned in an intersection portion of the word and bit lines and including a magnetoresistance element, the magnetoresistance element comprising

a free layer comprising a first ferromagnetic layer and a second ferromagnetic layer which face each other and whose magnetization directions are equal to each other, and a nonmagnetic film which intervenes between the first and second ferromagnetic layers the free layer being changeable in the magnetization directions on applying a magnetic field;

a first pinned layer comprising a third ferromagnetic layer which faces the free layer, the first pinned layer retaining a magnetization direction thereof on applying the magnetic field; and

a first nonmagnetic layer intervening between the free layer and the first pinned layer,

wherein the nonmagnetic film is a layer selected from the group consisting of a first layer made of silicon and having a thickness of 1.4 nm to 1.8 nm, a second layer made of germanium and having a thickness of 1.4 nm to 1.8 nm, a third layer made of Al_2O_3 and having a thickness of 1.0 nm, and a fourth layer made of AlN and having a thickness of 0.5 nm to 1.5 nm.

Claims 11-19 (Canceled).

20. (Currently Amended) The magnetic memory according to claim 5, wherein the ~~first~~ nonmagnetic ~~layer~~ film is the first layer.

21. (Currently Amended) The magnetic memory according to claim 5, wherein the ~~first~~ nonmagnetic ~~layer~~ film is the second layer.

22. (Currently Amended) The magnetic memory according to claim 5, wherein the ~~first~~ nonmagnetic ~~layer~~ film is the third layer.

23. (Currently Amended) The magnetic memory according to claim 5, wherein the ~~first~~ nonmagnetic ~~layer~~ film is the fourth layer.

24. (Currently Amended) The magnetic memory according to claim 10, wherein the ~~first~~ nonmagnetic ~~layer~~ film is the first layer.

25. (Currently Amended) The magnetic memory according to claim 10, wherein the ~~first~~ nonmagnetic ~~layer~~ film is the second layer.

26. (Currently Amended) The magnetic memory according to claim 10, wherein the ~~first~~ nonmagnetic ~~layer~~ film is the third layer.

27. (Currently Amended) The magnetic memory according to claim 10, wherein the ~~first~~ nonmagnetic ~~layer~~ film is the fourth layer.

28. (Previously Presented) The magnetic memory according to claim 5, wherein the magnetoresistance element further comprises:

a second pinned layer comprising a fourth ferromagnetic layer which faces the first pinned layer with the free layer interposed therebetween, the second pinned layer retaining a magnetization direction thereof on applying the magnetic field; and

a second nonmagnetic layer intervening between the free layer and the second pinned layer.

29. (Previously Presented) The magnetic memory according to claim 10, wherein the magnetoresistance element further comprises:

a second pinned layer comprising a fourth ferromagnetic layer which faces the first pinned layer with the free layer interposed therebetween, the second pinned layer retaining a magnetization direction thereof on applying the magnetic field; and

a second nonmagnetic layer intervening between the free layer and the second pinned layer.